

DualCool™ N-Channel NexFET™ Power MOSFETs

 Check for Samples: [CSD16325Q5C](#)

FEATURES

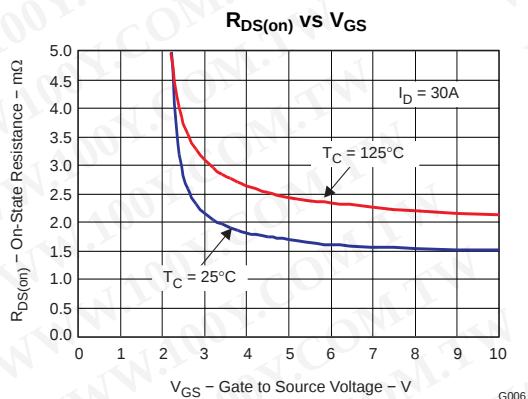
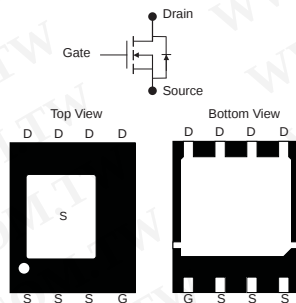
- DualCool™ Package SON 5×6mm
- Optimized for 2-Sided Cooling
- Optimized for 5V Gate Drive
- Ultralow Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant and Halogen Free

APPLICATIONS

- Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications.



PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V
Q_g	Gate Charge Total (4.5V)	18	nC
Q_{gd}	Gate Charge Gate to Drain	3.5	nC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3V$	2.1 mΩ
		$V_{GS} = 4.5V$	1.7 mΩ
		$V_{GS} = 8V$	1.5 mΩ
$V_{GS(th)}$	Threshold Voltage	1.1	V

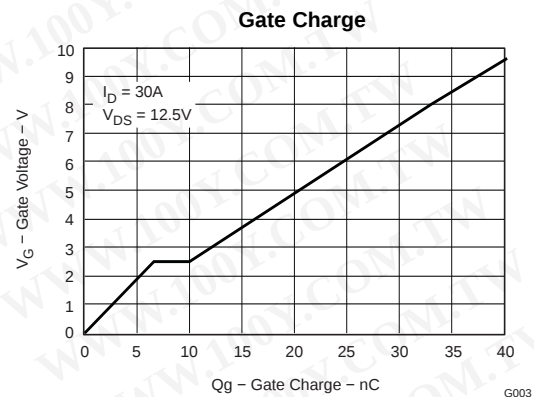
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16325Q5C	SON 5×6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ C$ unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -8	V
I_D	Continuous Drain Current, $T_C = 25^\circ C$	100	A
	Continuous Drain Current ⁽¹⁾	33	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ C$ ⁽²⁾	200	A
P_D	Power Dissipation ⁽¹⁾	3.1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ C$
E_{AS}	Avalanche Energy, single pulse $I_D = 100A, L = 0.1mH, R_G = 25\Omega$	500	mJ

- (1) Typical $R_{\theta JA} = 38^\circ C/W$ on 1-in² Cu, (2-oz.) on a 0.060" thick FR4 PCB.
- (2) Pulse duration $\leq 300\mu s$, duty cycle $\leq 2\%$



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

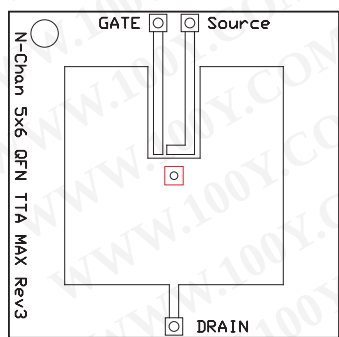
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = 250μA	25			V
I _{DSS}	Drain to Source Leakage	V _{GS} = 0V, V _{DS} = 20V			1	μA
I _{GSS}	Gate to Source Leakage	V _{DS} = 0V, V _{GS} = +10/−8V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.9	1.1	1.4	V
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 3V, I _D = 30A		2.1	2.9	mΩ
		V _{GS} = 4.5V, I _D = 30A		1.7	2.2	mΩ
		V _{GS} = 8V, I _D = 30A		1.5	2	mΩ
g _{fs}	Transconductance	V _{DS} = 15V, I _D = 30A		159		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		3070	4000	pF
C _{oss}	Output Capacitance			2190	2850	pF
C _{rss}	Reverse Transfer Capacitance			120	150	pF
R _G	Series Gate Resistance			1.6	3.2	Ω
Q _g	Gate Charge Total (4.5V)	V _{DS} = 12.5V, I _{DS} = 30A		18	25	nC
Q _{gd}	Gate Charge – Gate to Drain			3.5		nC
Q _{gs}	Gate Charge – Gate to Source			6.6		nC
Q _{g(th)}	Gate Charge at V _{th}			3.1		nC
Q _{oss}	Output Charge	V _{DS} = 13V, V _{GS} = 0V		43		nC
t _{d(on)}	Turn On Delay Time	V _{DS} = 12.5V, V _{GS} = 4.5V, I _{DS} = 30A , R _G = 2Ω		10.5		ns
t _r	Rise Time			16		ns
t _{d(off)}	Turn Off Delay Time			32		ns
t _f	Fall Time			12		ns
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{DS} = 30A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	V _{DD} = 13V, I _F = 30A, di/dt = 300A/μs		63		nC
t _{rr}	Reverse Recovery Time			47		ns

THERMAL CHARACTERISTICS

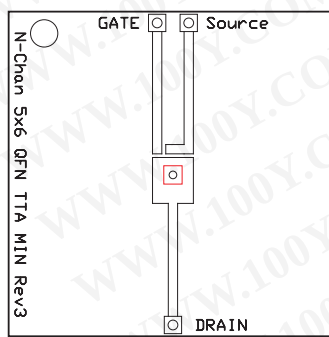
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			1.4	°C/W
R _{θJC}	Thermal Resistance Junction to Case (Bottom drain) ⁽¹⁾			1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			50	°C/W

- (1) R_{θJC} is determined with the device mounted on a 1-inch² 2-oz. Cu pad on a 1.5 × 1.5-inch 0.060-inch thick FR4 board. R_{θJC} is specified by design, whereas R_{θCA} is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch² of 2-oz. Cu.



Max $R_{\theta JA} = 50^{\circ}\text{C/W}$
when mounted on
1 inch² of 2-oz. Cu.



Max $R_{\theta JA} = 126^{\circ}\text{C/W}$
when mounted on
minimum pad area of
2-oz. Cu.

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TYPICAL MOSFET CHARACTERISTICS

($T_A = 25^{\circ}\text{C}$ unless otherwise stated)

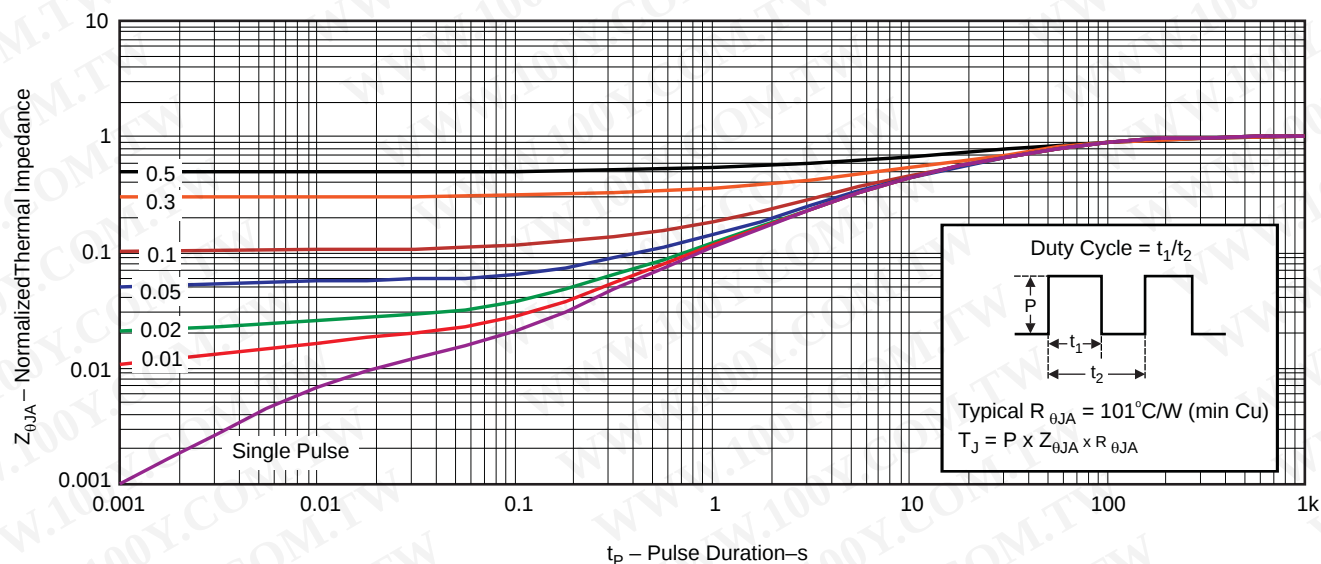
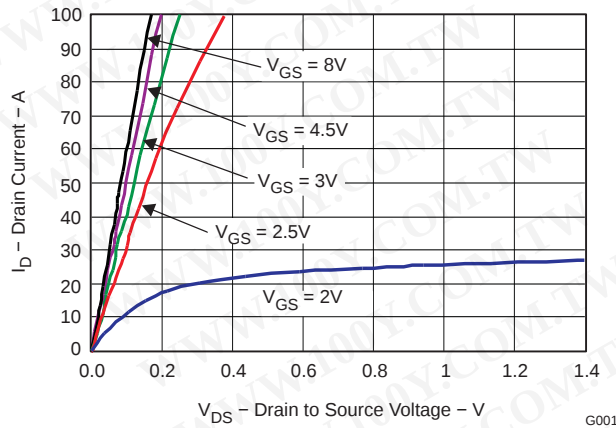
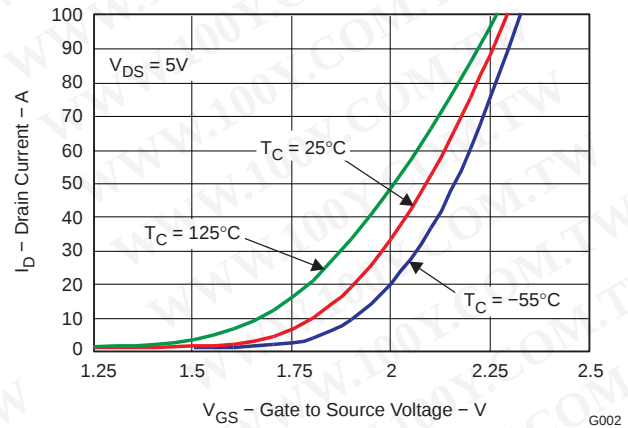
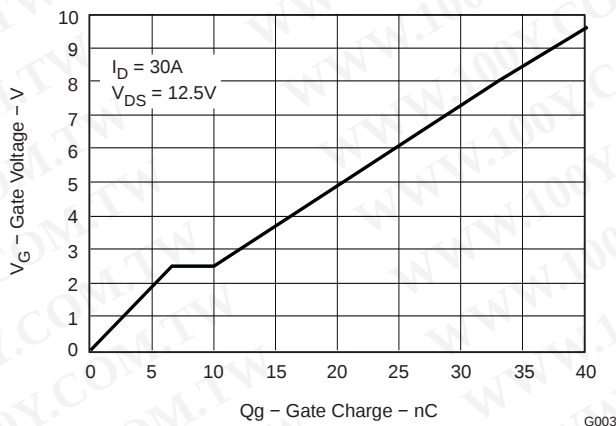
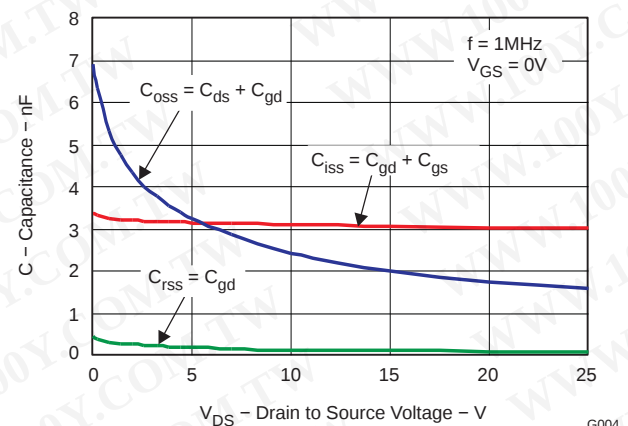
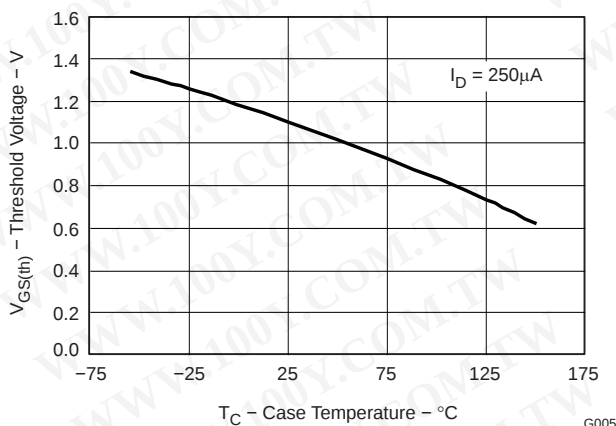
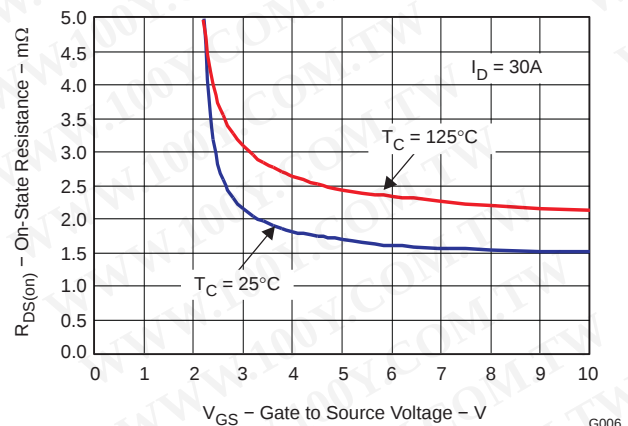


Figure 1. Transient Thermal Impedance

G012

TYPICAL MOSFET CHARACTERISTICS (continued)(T_A = 25°C unless otherwise stated)**Figure 2. Saturation Characteristics****Figure 3. Transfer Characteristics****Figure 4. Gate Charge****Figure 5. Capacitance****Figure 6. Threshold Voltage vs. Temperature****Figure 7. On Resistance vs. Gate Voltage**

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

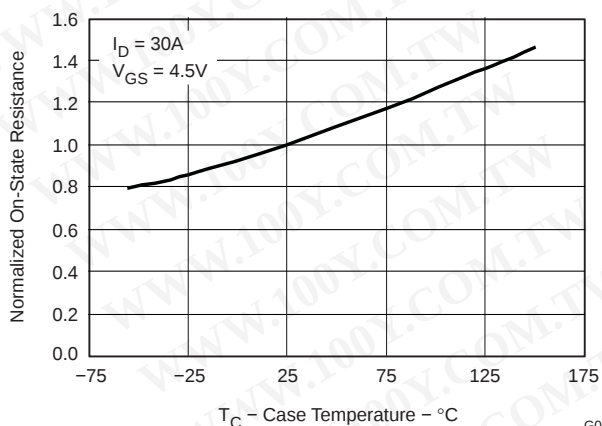


Figure 8. On Resistance vs. Temperature

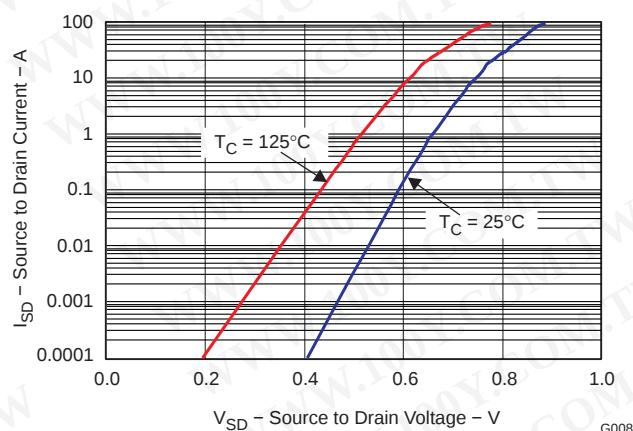


Figure 9. Typical Diode Forward Voltage

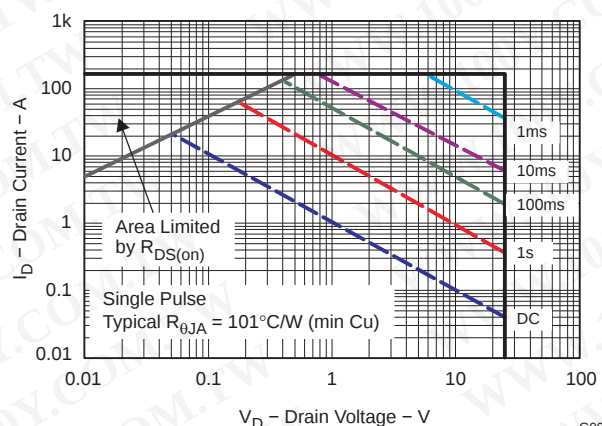


Figure 10. Maximum Safe Operating Area

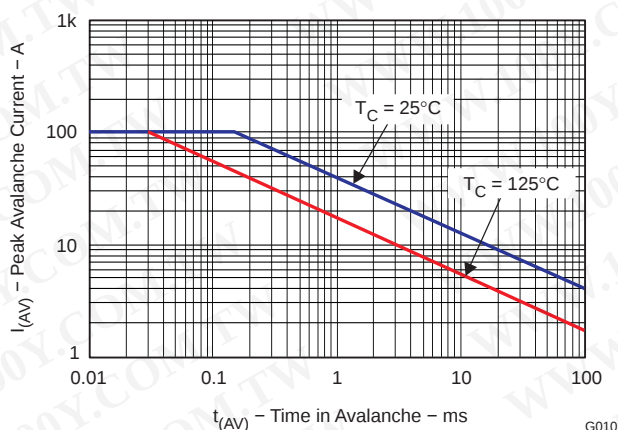


Figure 11. Single Pulse Unclamped Inductive Switching

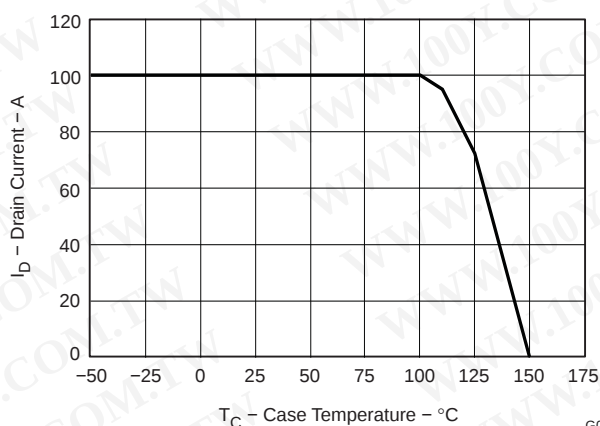
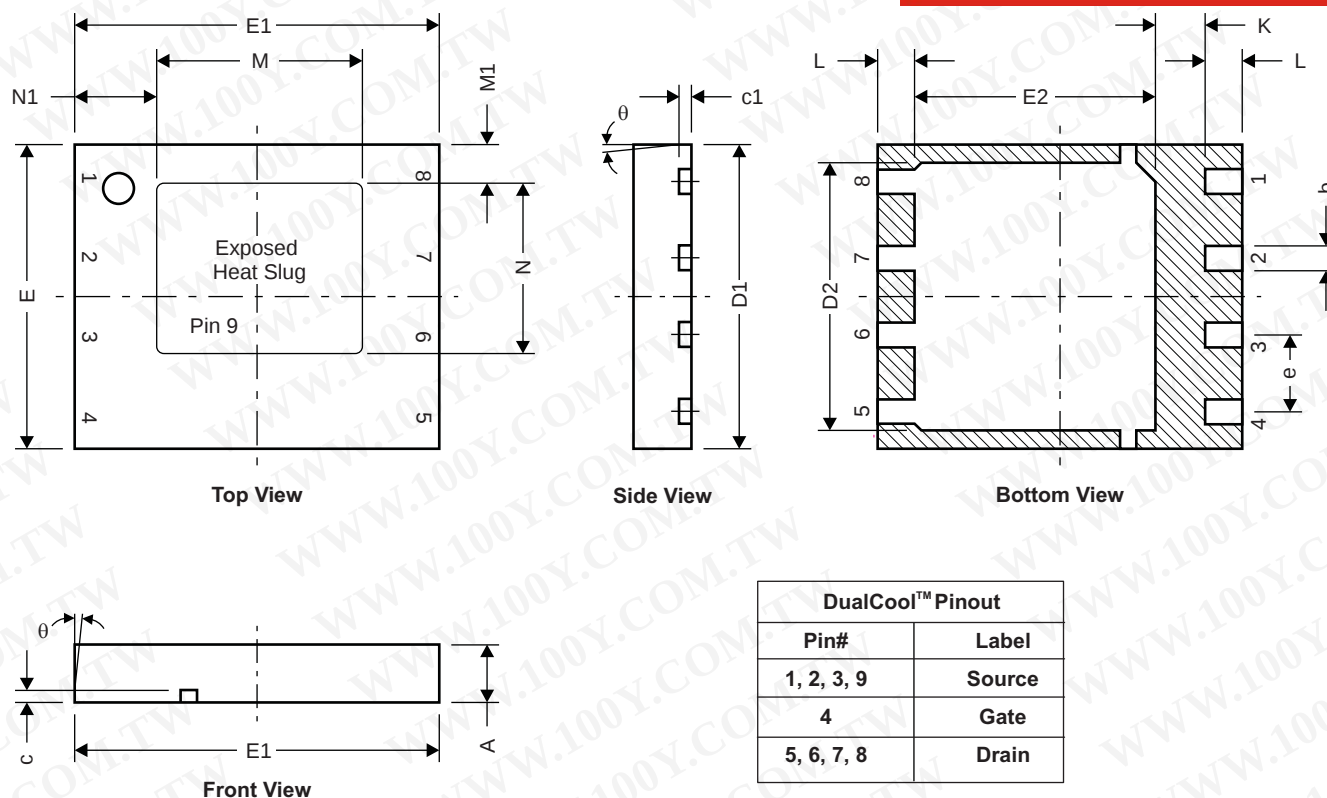


Figure 12. Maximum Drain Current vs. Temperature

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MECHANICAL DATA

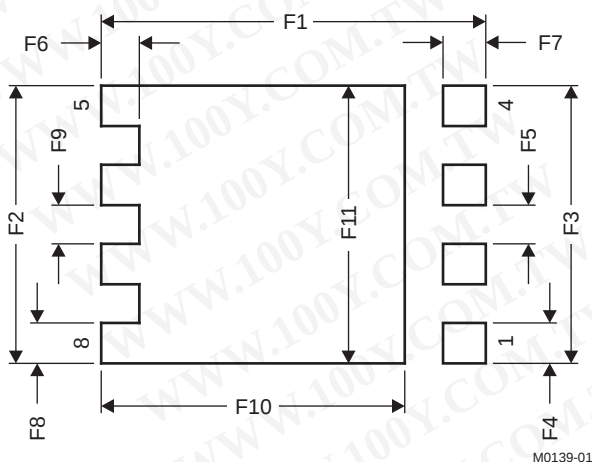
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Q5C Package Dimensions

M0162-01

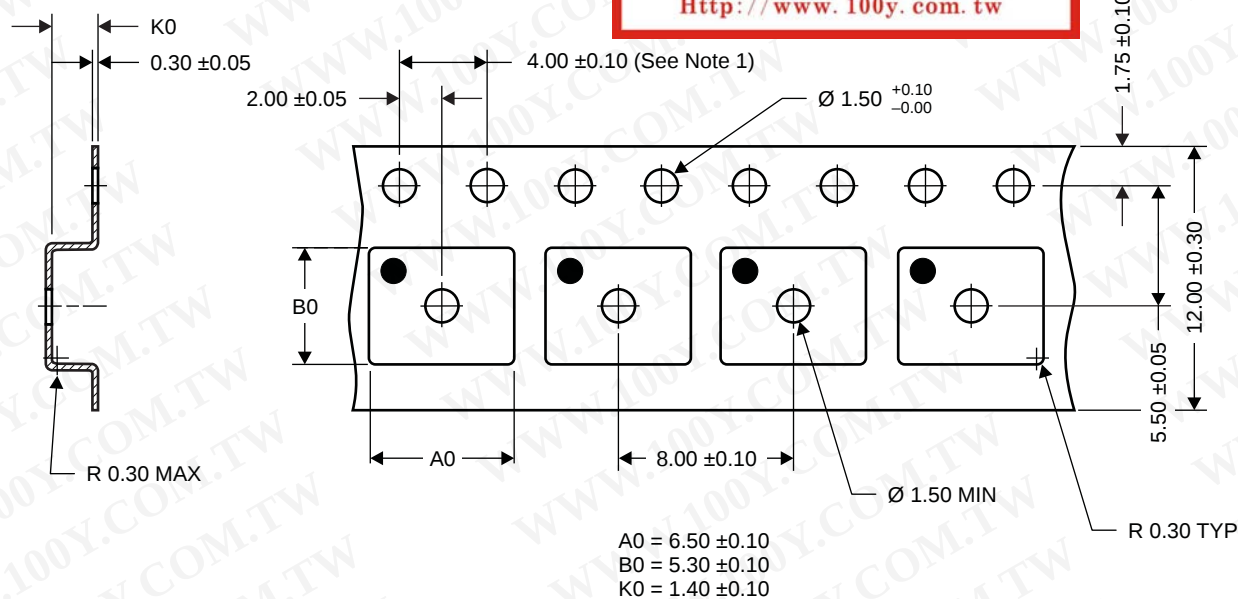
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
L	0.510	0.710	0.020	0.028
θ	–	–	–	–
K	0.760	–	0.030	–
M	3.260	3.460	0.128	0.136
M1	0.520	0.720	0.020	0.028
N	2.720	2.920	0.107	0.115
N1	1.227	1.427	0.048	0.056

Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

Q5C Tape and Reel Information



M0138-01

Notes:

1. 10-sprocket hole-pitch cumulative tolerance ± 0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm, unless otherwise specified.
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
6. MSL1 260°C (IR and convection) PbF reflow compatible

REVISION HISTORY

Changes from Original (December 2009) to Revision A	Page
- Changed the labels on the Bottom View pinout image - Changed the Mechanical Data dimensions table. Added dimensions for M, M1, N and N1	1 6
Changes from Revision A (April 2010) to Revision B	Page
- Changed $R_{DS(on)} - V_{GS} = 3V$ in the Electrical Characteristics table From: 2.7 To: 2.9 in the max column - Deleted the Package Marking Information section	2 7

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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
CSD16325Q5C	ACTIVE	SON	DQU	8	2500	Pb-Free (RoHS Exempt)	Call TI	Level-1-260C-UNLIM	Request Free Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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